	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	1	6297104.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/28 21:43
2	BRS	L2	5	5840602.pn. or 6150243.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/28 21:46
3	BRS	L3	2984	(logic adj1 device) and (memory adj1 device)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/28 21:47
4	BRS	L4	44	(first adj1 transistor) near10 (dielectric adj1 layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/28 21:58
5	BRS	L5	4	3 and 4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/28 21:51

	Type	L #	Hits	Search Text	DBs	Time Stamp
8	BRS	L6	49	(first adj1 transistor) near15 (dielectric adj1 layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/28 1:56
7	BRS	L7	4	3 and 6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/28 21:56
8	BRS	L8	5163	transistor near15 (dielectric adj1 layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/28 22:38
9	BRS	L9	79	3 and 8	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/28 21:57
10	BRS	L10	69	9 and thickness	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/28 21:57

	Type	L #	Hits	Search Text	DBs	Time Stamp
L11	BRS	L11	37	10 and channel adj1 region	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/28 21:58
L12	BRS	L12	13	11 and oxidation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/28 21:5?
L13	BRS	L13	35	11 and oxid$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/28 22:15
L14	BRS	L14		transistor near15 ((dielectric adj1 layer) r silicon adj1 dioxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/28 22:4?
L15	BRS	L15	17	3 and 14	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/28 22:46

	Type	L #	Hits	Search Text	DBs	Time Stamp
16	BRS	L16	100	15 and channel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/28 22:47
17	BRS	L17	89	16 and (source and drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/28 23:17
18	BRS	L18	407	3 and gate near1 oxide$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/28 23:18
19	BRS	L19	389	18 and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/28 23:18
					USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	

	Type	L #	Hits	Search Text	DBs	Time Stamp
	BRS	L21	288	20 and channel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/28 23:18
	BRS	L22	258	21 and (source and drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/28 23:18
	BRS	L23	129	22 and oxidation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/28 23:19
24	BRS	L24	258	22 and oxid$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/28 23:55
					USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	

	Type	L #	Hits	Search Text	DBs	Time Stamp
	BRS			...adj...adj1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/29
27	BRS	L27	0	(silicon adj1 dioxide and silicon adj1 nitride) near10 (high adj1 oxidation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/29 00:47
28	BRS	L28	128	(silicon adj1 dioxide near3 silicon adj1 nitride) near10 (oxidation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/29 00:49
	BRS	L29	1	3 and 28	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/29 00:50
	BRS	L30	91	28 and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/29 00:50

	Type	L #	Hits	Search Text	DBs	Time Stamp
31	BRS	L31	82	30 and high	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/29 00:54
32	BRS	L33	14	31 and (memory and logic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/29 00:54
33	BRS	L32	42	31 and (memory or logic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/03/29 01:03